

具有 400mV 基准电压的 TLV6713 低功耗 36V 比较器

1 特性

- 高电源电压范围：1.8V 至 36V
- 可调节阈值：低至 400mV
- 高阈值精度：
 - 0.25%（典型值）
 - 在工作温度范围内最高 0.75%
- 低静态电流：7 μ A（典型值）
- 漏极开路输出
- 内部滞后：5.5mV（典型值）
- 温度范围：-40°C 至 +125°C
- 封装：超薄 SOT-23-6

2 应用

- 笔记本电脑和平板电脑
- 智能手机
- 数码相机
- 视频游戏控制器
- 中继器和断路器
- 便携式医疗设备
- 门窗传感器
- 便携式和电池供电类产品

3 说明

TLV6713 是一款高电压比较器，工作电压范围为 1.8V 至 36V。该器件具有一个内部基准电压为 400mV 的高精度比较器以及一个额定电压为 25V 的开漏输出，用于实现欠压检测。监视电压可使用外部电阻进行设置。

当 SENSE 引脚的电压降至负向阈值以下时，OUT 被驱动为低电平；当 SENSE 引脚的电压升至正向阈值以上时，OUT 被驱动为高电平。TLV6713 中的比较器具有抑制噪声的内置迟滞，确保稳定的输出运行，不会引起误触发。

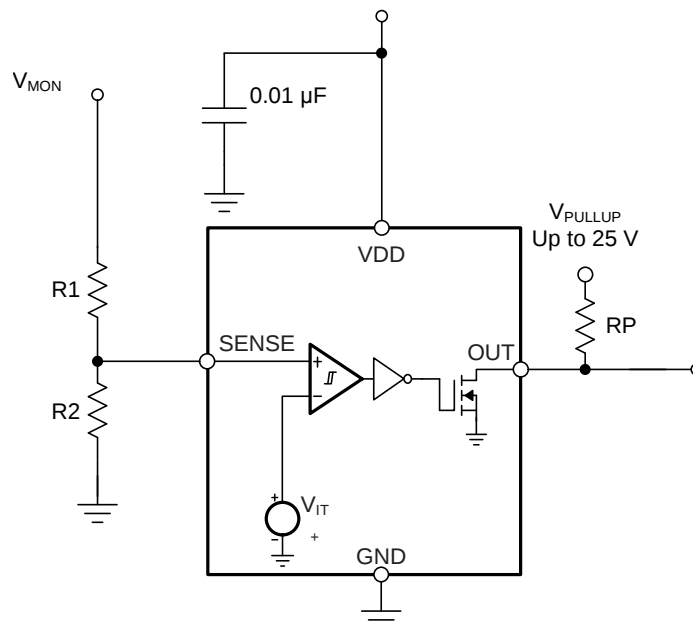
TLV6713 采用超薄 SOT-23-6 封装，额定结温范围为 -40°C 至 +125°C。

器件信息 (1)

器件型号	封装	封装尺寸（标称值）
TLV6713	SOT-23 (6)	2.90mm $\times$ 1.60mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的封装选项附录。

典型应用



目录

1	特性	1	8.3	Feature Description	9
2	应用	1	8.4	Device Functional Modes	9
3	说明	1	9	Application and Implementation	10
4	修订历史记录	2	9.1	Application Information	10
5	Device Comparison Table	2	9.2	Typical Application	11
6	Pin Configuration and Functions	3	10	Power Supply Recommendations	14
7	Specifications	4	11	Layout	15
7.1	Absolute Maximum Ratings	4	11.1	Layout Guidelines	15
7.2	ESD Ratings	4	11.2	Layout Example	15
7.3	Recommended Operating Conditions	4	12	器件和文档支持	16
7.4	Thermal Information	4	12.1	器件支持	16
7.5	Electrical Characteristics	5	12.2	接收文档更新通知	16
7.6	Timing Requirements	5	12.3	社区资源	16
7.7	Typical Characteristics	6	12.4	商标	16
8	Detailed Description	8	12.5	静电放电警告	16
8.1	Overview	8	12.6	术语表	16
8.2	Functional Block Diagram	8	13	机械、封装和可订购信息	16

4 修订历史记录

Changes from Revision A (April 2018) to Revision B	Page
• 已更改 将“典型应用”图中的上拉电阻器文字从 36V 更改为 25V	1

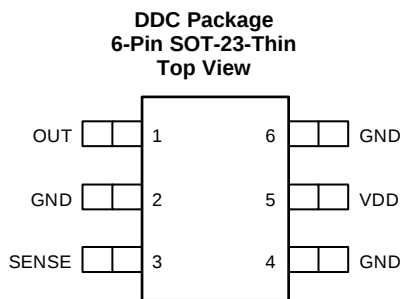
Changes from Original (January 2018) to Revision A	Page
• 已更改 将“预告信息”更改为“生产数据”	1

5 Device Comparison Table

Table 1. TLV67xx Integrated Comparator Family

PART NUMBER	CONFIGURATION	OPERATING VOLTAGE RANGE	THRESHOLD ACCURACY OVER TEMPERATURE
TLV6700	Window	1.8 V to 18 V	1%
TLV6703	Non-Inverting Single Channel	1.8 V to 18 V	1%
TLV6710	Window	1.8 V to 36 V	0.75%
TLV6713	Non-Inverting Single Channel	1.8 V to 36 V	0.75%

6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
GND	2, 4, 6	—	Ground. Connect all three pins to ground.
OUT	1	O	Comparator open-drain output. This pin is driven low when the voltage at this comparator is less than V_{IT-} . The output goes high when the sense voltage rises above V_{IT+} .
SENSE	3	I	Comparator input. This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this pin drops below the threshold voltage V_{IT-} , OUT is driven low.
VDD	5	I	Supply-voltage input. Connect a 1.8-V to 36-V supply to VDD to power the device. It is good analog design practice to place a 0.1- μ F ceramic capacitor close to this pin.

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Voltage ⁽²⁾	V _{DD}	−0.3	40	V
	V _{OUT}	−0.3	28	
	V _{SENSE}	−0.3	7	
Current	Output pin current		40	mA
Temperature	Operating junction, T _J	−40	125	°C
	Storage, T _{stg}	−40	125	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network ground terminal.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	Supply pin voltage	1.8		36	V
V _{SENSE}	Input pin voltage	0		1.7	V
V _{OUT}	Output pin voltage	0		25	V
V _{PULLUP}	Pullup voltage	0		25	V
I _{OUT}	Output pin current	0		10	mA
T _J	Junction temperature	−40	25	125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV6713	UNIT
		DDC (SOT-23)	
		6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	201.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	47.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	51.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	50.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

Over the operating temperature range of $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $1.8\text{ V} \leq V_{DD} < 36\text{ V}$, and pullup resistor $R_P = 100\text{ k}\Omega$ (unless otherwise noted). Typical values are at $T_J = 25^{\circ}\text{C}$ and $V_{DD} = 12\text{ V}$.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(POR)}$ Power-on reset voltage ⁽¹⁾	$V_{OL} \leq 0.2\text{ V}$			0.8	V
V_{IT-} SENSE pin negative input threshold voltage	$V_{DD} = 1.8\text{ V}$ to 36 V	397	400	403	mV
V_{IT+} SENSE pin positive input threshold voltage	$V_{DD} = 1.8\text{ V}$ to 36 V	400	405.5	413	mV
V_{HYS} SENSE pin hysteresis voltage ($HYS = V_{IT+} - V_{IT-}$)		2	5.5	12	mV
V_{OL} Low-level output voltage	$V_{DD} = 1.8\text{ V}$, $I_{OUT} = 3\text{ mA}$		130	250	mV
	$V_{DD} = 5\text{ V}$, $I_{OUT} = 5\text{ mA}$		150	250	
I_{IN} Input current (at SENSE pin)	$V_{DD} = 1.8\text{ V}$ and 36 V , $V_{SENSE} = 6.5\text{ V}$	-25	+1	+25	nA
	$V_{DD} = 1.8\text{ V}$ and 36 V , $V_{SENSE} = 0.1\text{ V}$	-15	+1	+15	
$I_{D(leak)}$ Open-drain leakage current	$V_{DD} = 1.8\text{ V}$ and 36 V , $V_{OUT} = 25\text{ V}$		10	300	nA
I_{DD} Supply current	$V_{DD} = 1.8\text{ V} - 36\text{ V}$		8	11	μA
UVLO Undervoltage lockout ⁽²⁾	V_{DD} falling	1.3	1.5	1.7	V

(1) The lowest supply voltage (V_{DD}) at which output is active; $t_{(VDD)} > 15\text{ }\mu\text{s/V}$. If less than $V_{(POR)}$, the output is undetermined.

(2) When V_{DD} falls below UVLO, OUT is driven low. The output cannot be determined if less than $V_{(POR)}$.

7.6 Timing Requirements

		MIN	NOM	MAX	UNIT
$t_{pd(HL)}$ High-to-low propagation delay ⁽¹⁾	$V_{DD} = 24\text{ V}$, $\pm 10\text{-mV}$ input overdrive, $R_L = 100\text{ k}\Omega$, $V_{OH} = 0.9 \times V_{DD}$, $V_{OL} = 250\text{ mV}$		9.9		μs
$t_{pd(LH)}$ Low-to-high propagation delay ⁽¹⁾	$V_{DD} = 24\text{ V}$, $\pm 10\text{-mV}$ input overdrive, $R_L = 100\text{ k}\Omega$, $V_{OH} = 0.9 \times V_{DD}$, $V_{OL} = 250\text{ mV}$		28.1		μs
$t_{d(start)}$ Startup delay ⁽²⁾	$V_{DD} = 5\text{ V}$		155		μs
t_r Output rise time	$V_{DD} = 12\text{ V}$, 10-mV input overdrive, $R_L = 100\text{ k}\Omega$, $C_L = 10\text{ pF}$, $V_O = (0.1\text{ to }0.9) \times V_{DD}$		2.7		μs
t_f Output fall time	$V_{DD} = 12\text{ V}$, 10-mV input overdrive, $R_L = 100\text{ k}\Omega$, $C_L = 10\text{ pF}$, $V_O = (0.9\text{ to }0.1) \times V_{DD}$		0.12		μs

(1) High-to-low and low-to-high refers to the transition at the input pin (SENSE).

(2) During power on, V_{DD} must exceed 1.8 V for at least $150\text{ }\mu\text{s}$ (typical) before the output state reflects the input condition.

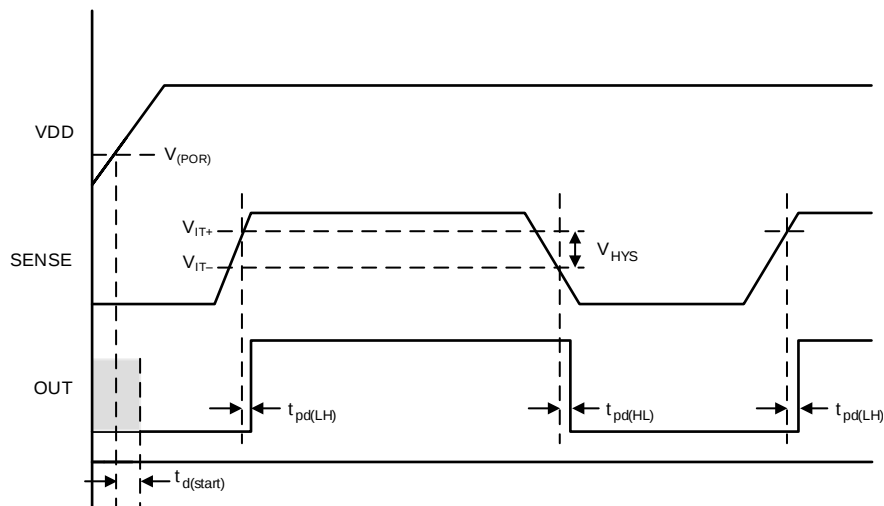


Figure 1. Timing Diagram

7.7 Typical Characteristics

at $T_J = 25^\circ\text{C}$ and $V_{DD} = 12\text{ V}$ (unless otherwise noted)

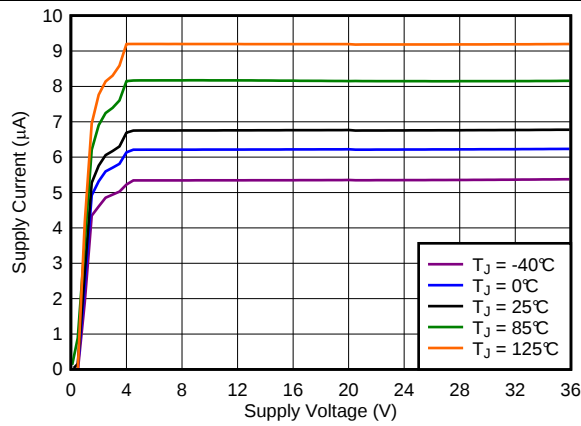
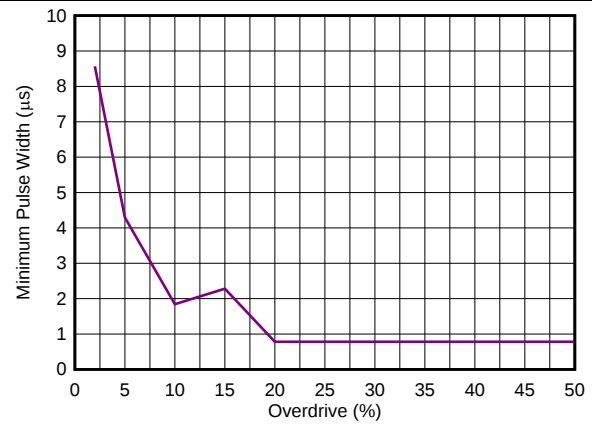


Figure 2. Supply Current vs Supply Voltage



$V_{DD} = 24\text{ V}$, minimum pulse duration required to trigger output high-to-low transition, SENSE = negative spike below V_{IT-}

Figure 3. Minimum Pulse Duration vs Threshold Overdrive Voltage

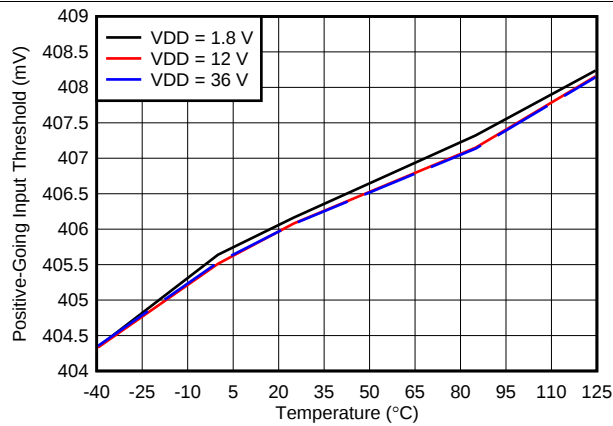


Figure 4. SENSE Positive Input Threshold Voltage (V_{IT+}) vs Temperature

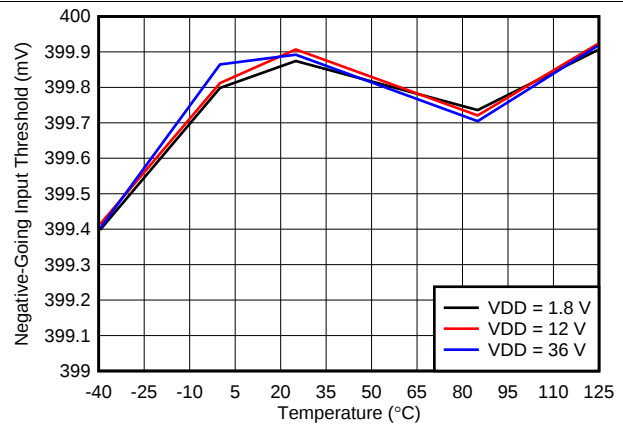


Figure 5. SENSE Negative Input Threshold Voltage (V_{IT-}) vs Temperature

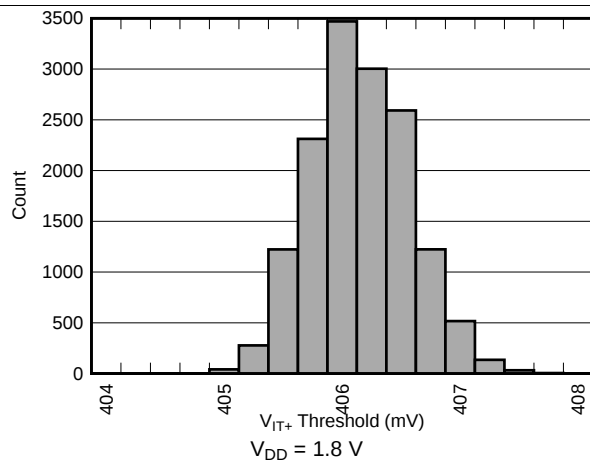


Figure 6. SENSE Positive Input Threshold Voltage (V_{IT+}) Distribution

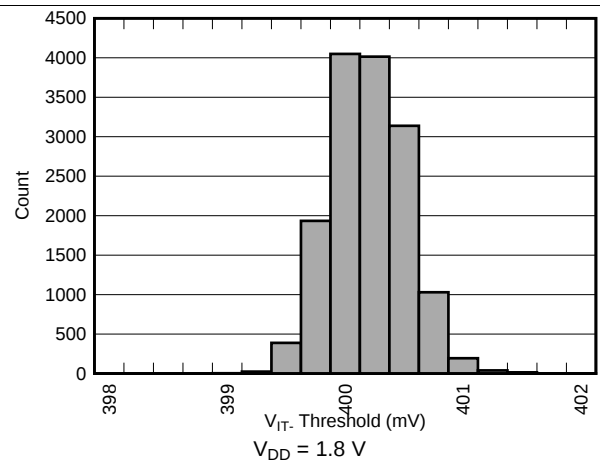
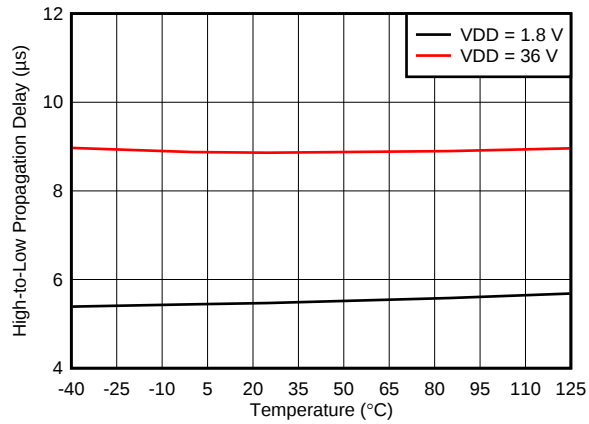


Figure 7. SENSE Negative Input Threshold Voltage (V_{IT-}) Distribution

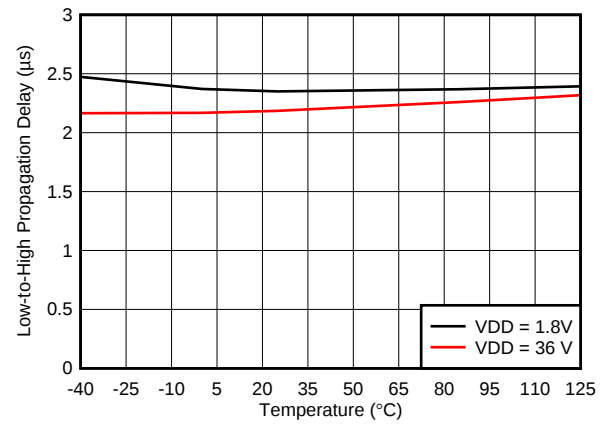
Typical Characteristics (continued)

at $T_J = 25^\circ\text{C}$ and $V_{DD} = 12\text{ V}$ (unless otherwise noted)



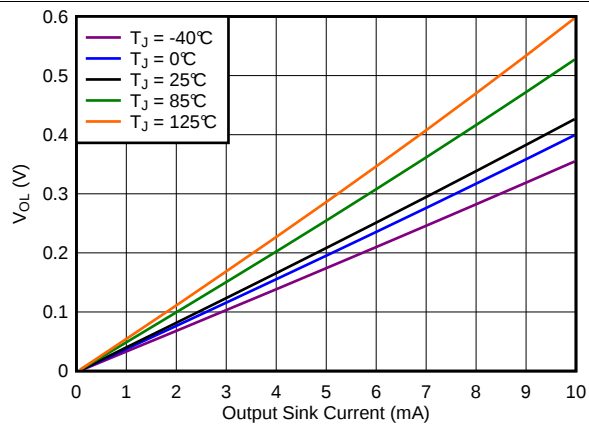
Input step $\pm 200\text{ mV}$

**Figure 8. Propagation Delay vs Temperature
(High-to-Low Transition at SENSE)**



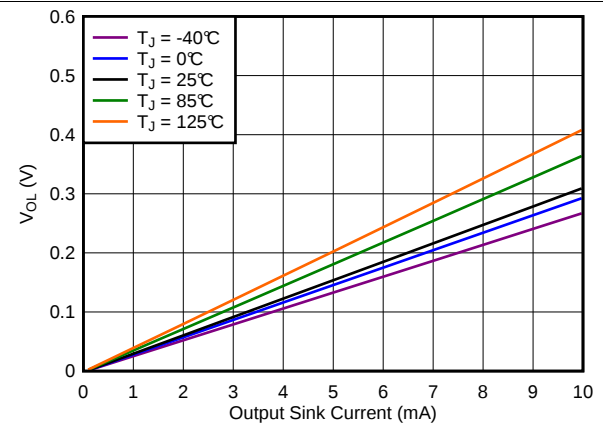
Input step $\pm 200\text{ mV}$

**Figure 9. Propagation Delay vs Temperature
(Low-to-High Transition at SENSE)**



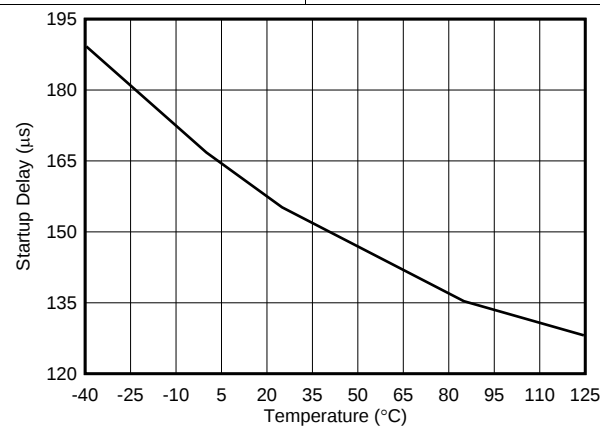
$V_{DD} = 1.8\text{ V}$

Figure 10. Output Voltage Low vs Output Sink Current



$V_{DD} = 12\text{ V}$

Figure 11. Output Voltage Low vs Output Sink Current



$V_{DD} = 5\text{ V}$

Figure 12. Start-up Delay vs Temperature

8 Detailed Description

8.1 Overview

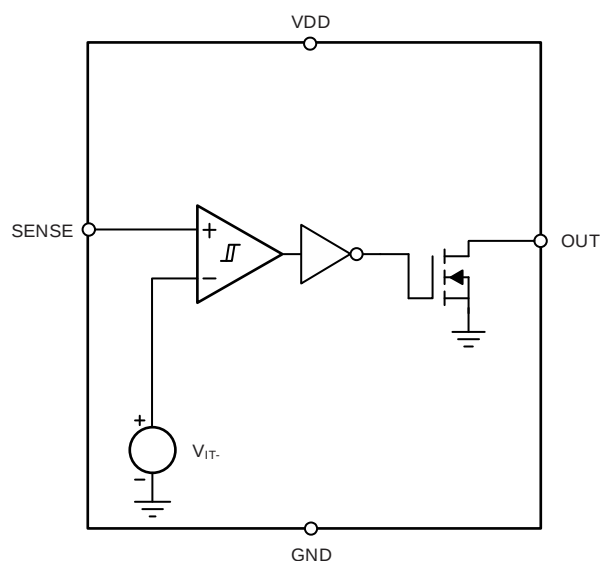
The TLV6713 combines a comparator and a precision reference for undervoltage detection. The TLV6713 features a wide supply voltage range (1.8 V to 36 V) and a high-accuracy threshold voltage of 400 mV (0.75% over temperature) with built-in hysteresis. The output is rated to 25 V and can sink up to 10 mA.

Set the input pin (SENSE) to monitor any voltage above 0.4 V by using an external resistor divider network. SENSE has very low input leakage current, allowing the use of a large resistor divider without sacrificing system accuracy. The relationship between the input and the output is shown in [Table 2](#). Broad voltage thresholds are supported that enable the device to be used in a wide array of applications.

Table 2. Truth Table

CONDITION	OUTPUT	OUTPUT STATE
$\text{SENSE} > V_{IT+}$	OUT high	Output high impedance
$\text{SENSE} < V_{IT-}$	OUT low	Output sinking

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Input Pin (SENSE)

The TLV6713 combines a comparator with a precision reference voltage. The comparator has one external input and one internal input connected to the internal reference. The falling threshold on SENSE is designed and trimmed to be equal to the reference voltage (400 mV). This configuration optimizes the device accuracy. The comparator also has built-in hysteresis that proves immunity to noise and ensures stable operation.

The comparator input swings from ground to 1.7 V (7 V absolute maximum), regardless of the device supply voltage used. Although not required in most cases, it is good analog design practice to place a 1-nF to 10-nF bypass capacitor at the comparator input for noisy applications to reduce sensitivity to transient voltage changes on the monitored signal.

For the comparator, the output (OUT) is driven to logic low when the input SENSE voltage drops below V_{IT-} . When the voltage exceeds V_{IT+} , OUT goes to a high-impedance state; see [Figure 1](#).

8.3.2 Output Pin (OUT)

In a typical TLV6713 application, the output is connected to a GPIO input of the processor (such as a digital signal processor [DSP], central processing unit [CPU], field-programmable gate array [FPGA], or application-specific integrated circuit [ASIC]).

The TLV6713 provides an open-drain output (OUT) rated to 25 V, independent of supply voltage, and can sink up to 40 mA. A pullup resistor is required to hold the line high when the output goes to a high-impedance state. Connect this pullup resistor to a voltage rail that meets the logic requirements of the downstream device. To ensure the proper voltage level, give some consideration when choosing the pullup resistor value. The pullup resistor value is determined by V_{OL} , output capacitive loading, and the open-drain leakage current ($I_{D(leak)}$). These values are specified in the [Electrical Characteristics](#) table.

[Table 2](#) and [Input Pin \(SENSE\)](#) describe how the output is asserted or high impedance. See [Figure 1](#) for a timing diagram that describes the relationship between threshold voltage and the respective output.

8.4 Device Functional Modes

8.4.1 Normal Operation ($V_{DD} > UVLO$)

When the voltage on VDD is greater than 1.8 V for at least 155 μ s, the OUT signal corresponds to the voltage on SENSE, as listed in [Table 2](#).

8.4.2 Undervoltage Lockout ($V_{(POR)} < V_{DD} < UVLO$)

When the voltage on VDD is less than the device UVLO voltage, and greater than the power-on reset voltage, $V_{(POR)}$, the OUT signal is asserted regardless of the voltage on SENSE.

8.4.3 Power On Reset ($V_{DD} < V_{(POR)}$)

When the voltage on VDD is lower than the required voltage to internally pull the asserted output to GND ($V_{(POR)}$), OUT is in a high-impedance state.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TLV6713 is used as a precision voltage supervisor in several different configurations. The monitored voltage (V_{MON}), VDD voltage, and output pullup voltage can be independent voltages or connected in any configuration. The following sections show the connection configurations and the voltage limitations for each configuration.

9.1.1 Input and Output Configurations

Figure 13 and Figure 14 show examples of the various input and output configurations.

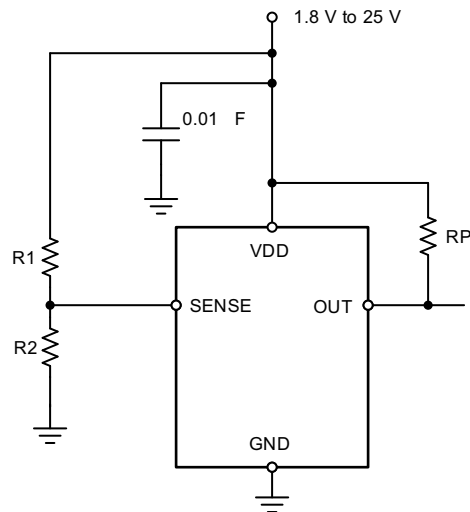
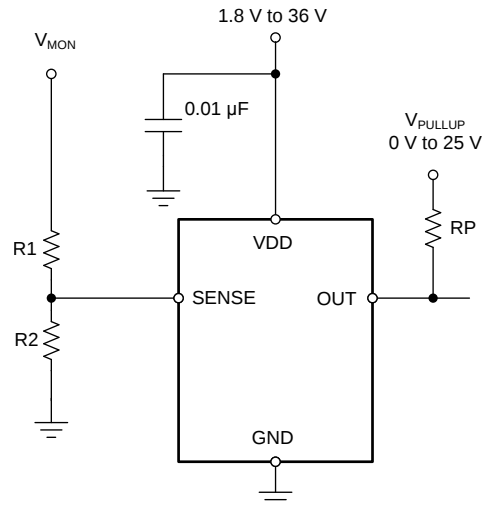


Figure 13. Monitoring the Same Voltage as V_{DD}

Application Information (continued)



NOTE: The input can monitor a voltage higher than V_{DD} (maximum) with the use of an external resistor divider network.

Figure 14. Monitoring a Voltage Other than V_{DD}

9.1.2 Immunity to Input Pin Voltage Transients

The TLV6713 is immune to short voltage transient spikes on the input pin. Sensitivity to transients depends on both transient duration and amplitude; see [Figure 3, Minimum Pulse Duration vs Threshold Overdrive Voltage](#).

9.2 Typical Application

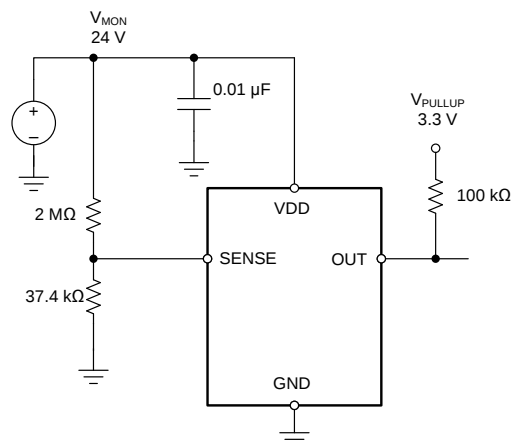


Figure 15. 24-V, 10% Comparator

Typical Application (continued)

9.2.1 Design Requirements

This typical voltage detector application is designed to meet the parameters listed in [Table 3](#):

Table 3. Design Parameters

PARAMETER	DESIGN REQUIREMENT	DESIGN RESULT
Monitored voltage	24-V nominal, falling ($V_{MON(UV)}$) threshold 10% nominal (21.6 V)	$V_{MON(UV)} = 21.8 \text{ V} \pm 2.7\%$
Output logic voltage	3.3-V CMOS	3.3-V CMOS
Maximum current consumption	30 μA	24 μA

9.2.2 Detailed Design Procedure

9.2.2.1 Resistor Divider Selection

The resistor divider values and target threshold voltage can be calculated by using [Equation 1](#) to determine $V_{MON(UV)}$.

$$V_{MON(UV)} = \left(1 + \frac{R1}{R2} \right) \times V_{IT}$$

where

- R1 and R2 are the resistor values for the resistor divider on the SENSE pin
 - $V_{MON(UV)}$ is the target voltage at which an undervoltage condition is detected
- (1)

Choose an R_{TOTAL} ($= R1 + R2$) so that the current through the divider is approximately 100 times higher than the input current at the SENSE pin. Use resistors with high values to minimize current consumption (as a result of low input bias current) without adding significant error to the resistive divider. For details on sizing input resistors, refer to [Optimizing Resistor Dividers at a Comparator Input](#), available for download from www.ti.com.

9.2.2.2 Pullup Resistor Selection

To ensure the proper logic-high voltage level (V_{HI}), select a pullup resistor value where the pullup voltage divided by the pullup resistor value does not exceed the sink-current capability of the device. Confirm this voltage level by verifying that the pullup voltage minus the open-drain leakage current ($I_{D(leak)}$) multiplied by the resistor is greater than the desired V_{HI} . These values are specified in the [Electrical Characteristics](#).

Use [Equation 2](#) to calculate the value of the pullup resistor.

$$\frac{V_{HI} - V_{pullup}}{I_{D(leak)}} \leq RP \leq \frac{V_{pullup}}{I_{OUT}}$$
(2)

9.2.2.3 Input Supply Capacitor

Although an input capacitor is not required for stability, for good analog design practice, connect a 0.1- μF low equivalent series resistance (ESR) capacitor across the VDD and GND pins. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is not located close to the power source.

9.2.3 Application Curve

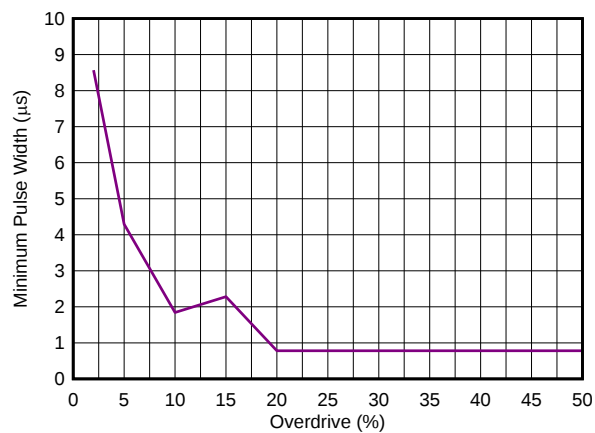


Figure 16. 24-V Window Monitor Output Response

10 Power Supply Recommendations

The TLV6713 has a 40-V absolute maximum rating on the VDD pin, with a recommended maximum operating condition of 36 V. If the voltage supply that provides power to VDD is susceptible to any large voltage transient that may exceed 40 V, or if the supply exhibits high voltage slew rates greater than 1 V/ μ s, then place an RC filter between the supply and VDD to filter any high-frequency transient surges on the VDD pin. In these cases, a 100- Ω resistor and 0.01- μ F capacitor are required, as shown in [Figure 17](#).

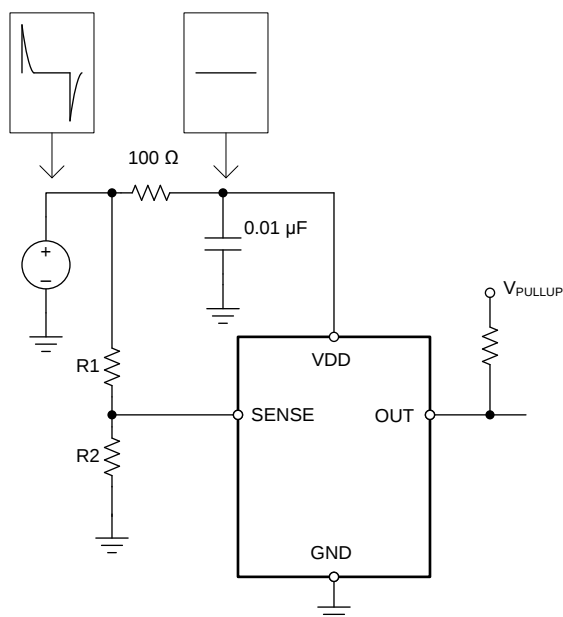


Figure 17. Using a RC Filter to Remove High-Frequency Disturbances on V_{DD}

11 Layout

11.1 Layout Guidelines

- Place R2 and R2 close to the device to minimize noise coupling into the SENSE node.
- Place the VDD decoupling capacitor close to the device.
- Avoid using long traces for the VDD supply node. The VDD capacitor (C_{VDD}), along with parasitic inductance from the supply to the capacitor, might form an LC tank and create ringing with peak voltages above the maximum VDD voltage. If long traces are unavoidable, see [Figure 17](#) for an example of filtering VDD.

11.2 Layout Example

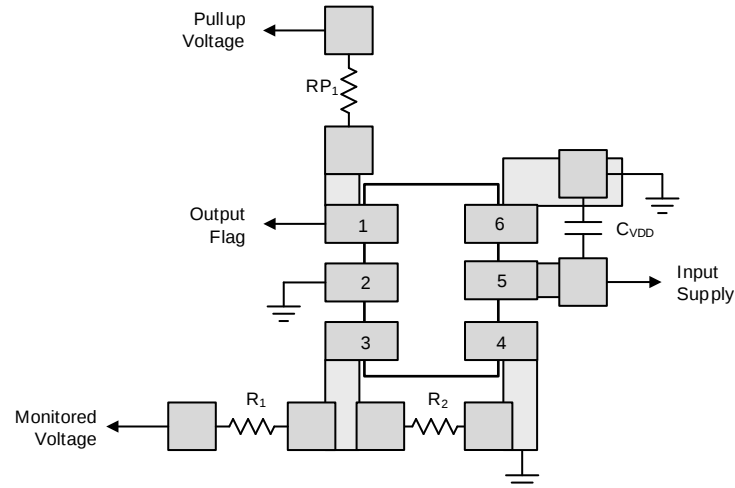


Figure 18. Recommended Layout

12 器件和文档支持

12.1 器件支持

12.1.1 开发支持

DIP 适配器评估模块可以将 SOT-23-6 封装转换为标准 DIP-6 引脚排列以便轻松构建原型和进行工作台评估。

12.2 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的 **通知我** 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

TI E2E™ 在线社区 **TI 的工程师对工程师 (E2E) 社区**。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 **TI 参考设计支持** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.4 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 术语表

SLYZ022 — **TI 术语表**。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV6713DDCR	Active	Production	SOT-23-THIN (DDC) 6	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1
TLV6713DDCR.A	Active	Production	SOT-23-THIN (DDC) 6	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1
TLV6713DDCT	Active	Production	SOT-23-THIN (DDC) 6	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1
TLV6713DDCT.A	Active	Production	SOT-23-THIN (DDC) 6	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1
TLV6713DDCTG4	Active	Production	SOT-23-THIN (DDC) 6	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1
TLV6713DDCTG4.A	Active	Production	SOT-23-THIN (DDC) 6	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1II1

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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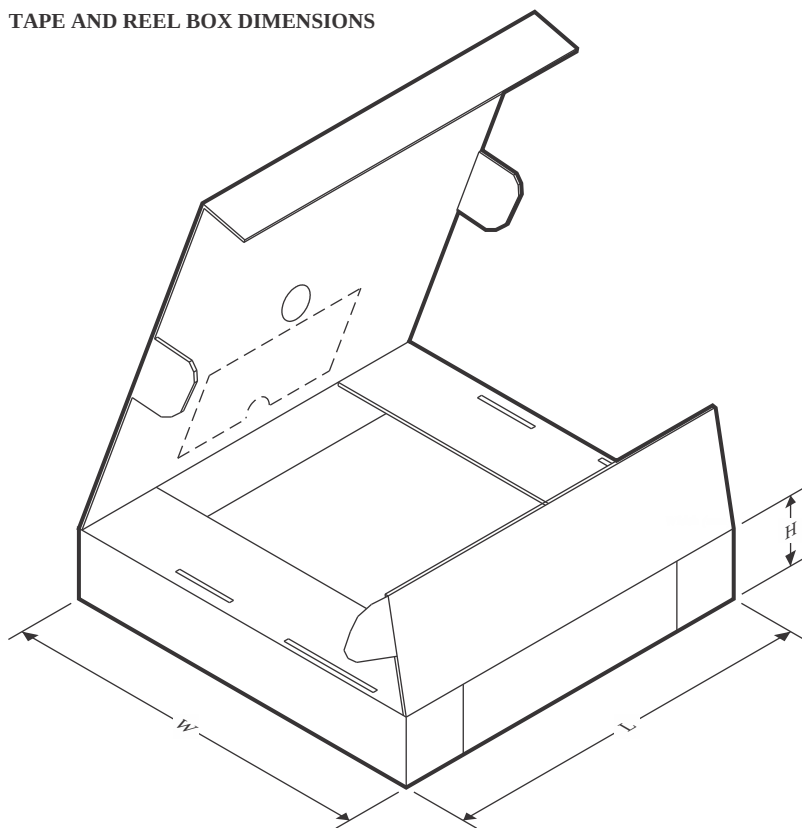
TAPE AND REEL INFORMATION



*All dimensions are nominal

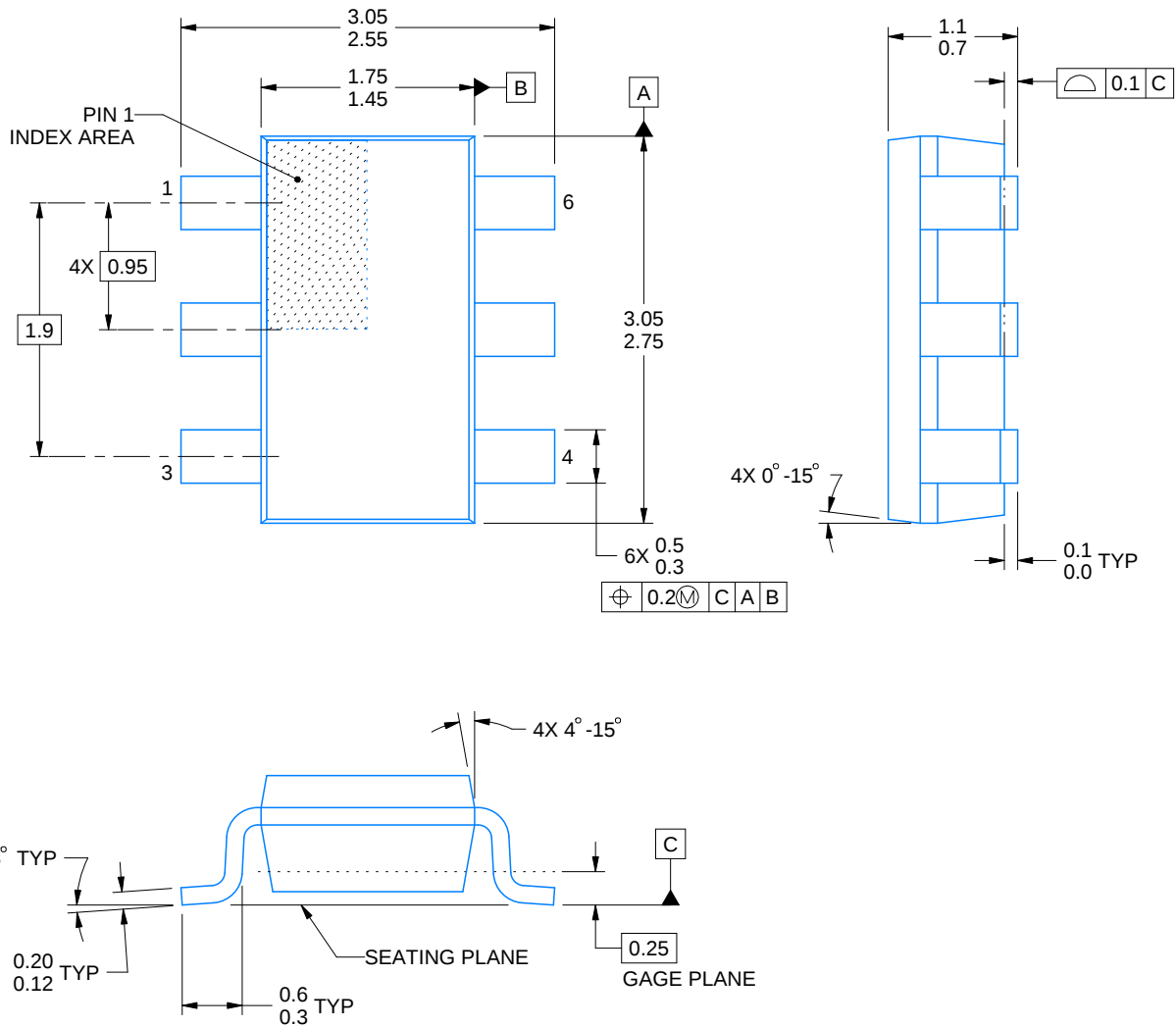
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV6713DDCR	SOT-23-THIN	DDC	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6713DDCT	SOT-23-THIN	DDC	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6713DDCTG4	SOT-23-THIN	DDC	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV6713DDCR	SOT-23-THIN	DDC	6	3000	213.0	191.0	35.0
TLV6713DDCT	SOT-23-THIN	DDC	6	250	213.0	191.0	35.0
TLV6713DDCTG4	SOT-23-THIN	DDC	6	250	213.0	191.0	35.0



4214841/E 08/2024

NOTES:

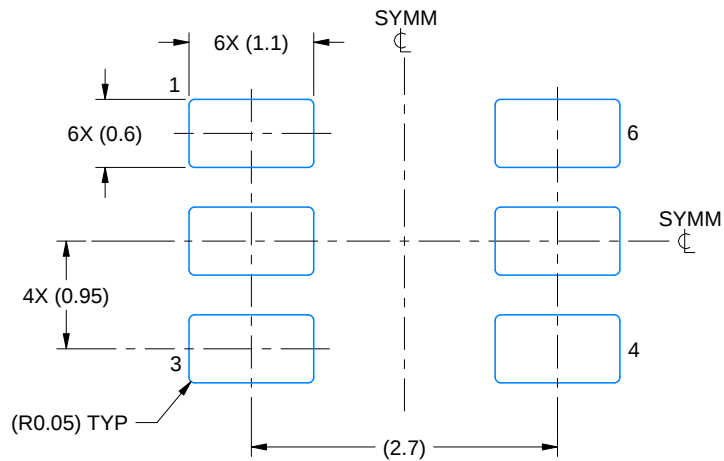
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-193.

EXAMPLE BOARD LAYOUT

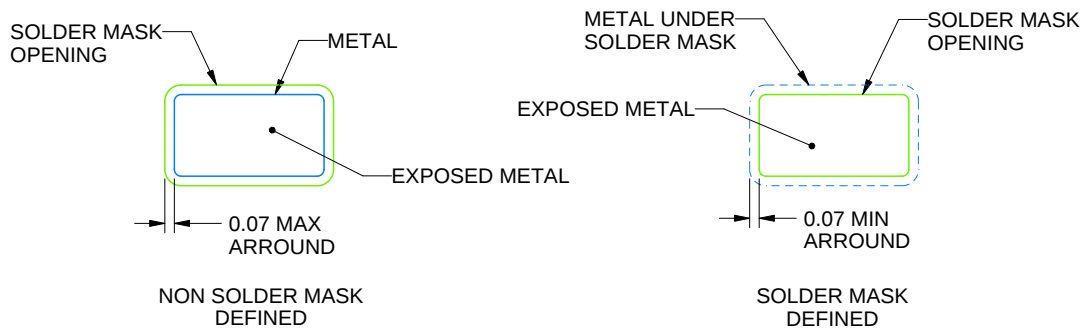
DDC0006A

SOT-23 - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPLODED METAL SHOWN
SCALE:15X

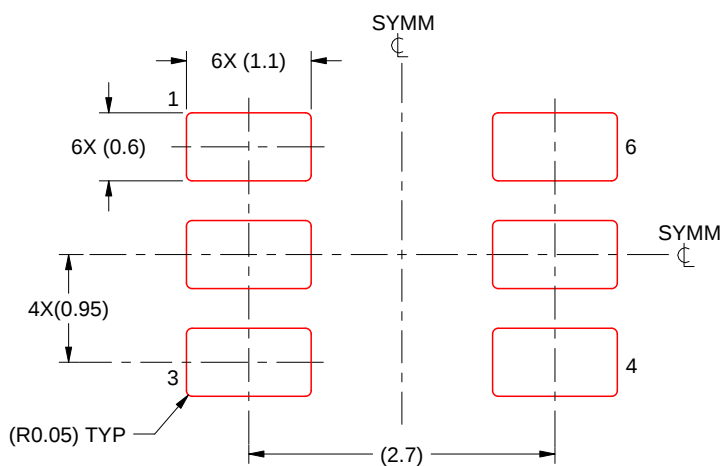


SOLDERMASK DETAILS

4214841/E 08/2024

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214841/E 08/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

重要通知和免责声明

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